



The JOC355 combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic SOP4 package. With the robust coplanar double mold structure, JOC355 provides the most stable isolation feature. The products are widely used in sequence controller telephone/fax, system appliances, measuring instrument and programmable logic controller.

Current transfer ratio CTR: 600%-7500% @ $I_F=1\text{mA}$, $V_{CE}=2\text{V}$

High isolation voltage between input and output

($V_{iso}=3,750\text{Vrms}$)

Operating temperature up to $+110^\circ\text{C}$

Collector-Emitter voltage $BV_{CEO} \geq 40\text{V}$

CQC approved

VDE approved

UL approved

The products comply with REACH and HF

(Temperature= 25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	60	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	100	mW
	Collector-emitter Voltage	V_{CEO}	40	V

Output

Isolation Voltage	V_{iso}	3750	Vrms
Operating Temperature	T_{opr}	-55~+110	
Storage Temperature	T_{stg}	-55~+	

FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

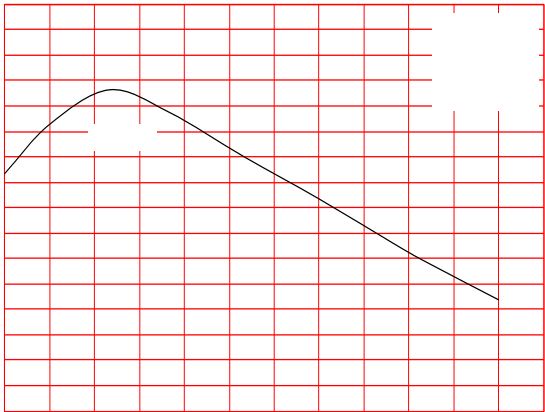


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

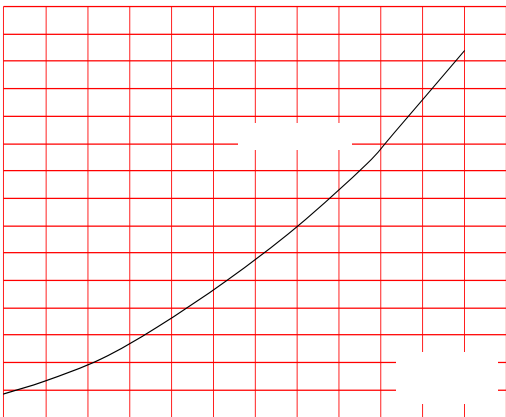


FIG.9: Response Time vs. Load Resistance

FIG.10: Frequency Response

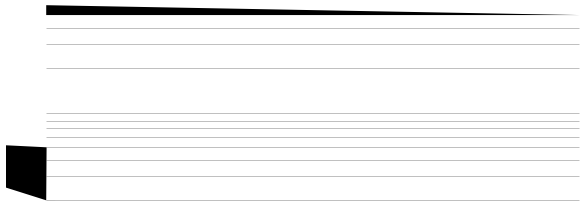


FIG.11: Test Circuits of Response Time

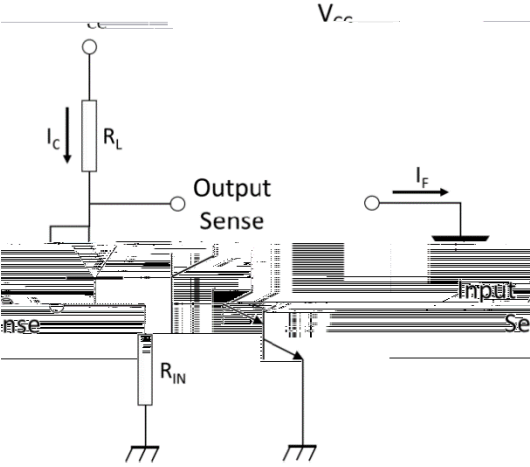


FIG.12: Curves of Response Time

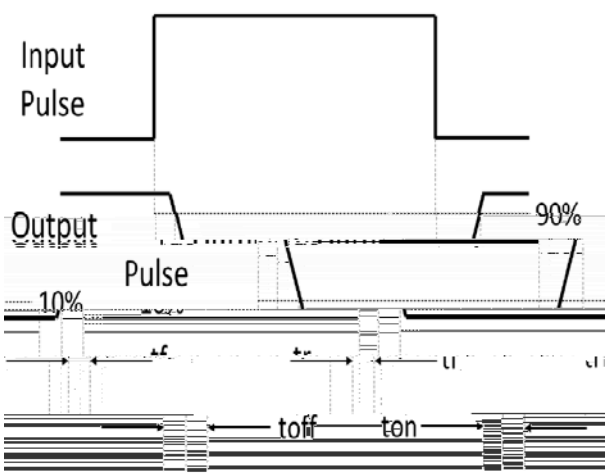


FIG.13: Test Circuits of Frequency Response

